

## 2SK4022

Switching Regulator, DC/DC Converter and Motor Drive Applications

- 4 V gate drive
- Low drain-source ON-resistance:  $R_{DS(ON)} = 1.2 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 2.2 S$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \mu A$  ( $V_{DS} = 250 V$ )
- Enhancement mode:  $V_{th} = 1.5\sim 3.5 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

### Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristic		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	250	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )		$V_{DGR}$	250	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	3	A
	Pulse ( $t = 1 ms$ ) (Note 1)	$I_{DP}$	6	
Drain power dissipation ( $T_c = 25^\circ C$ )		$P_D$	20	W
Single-pulse avalanche energy (Note 2)		$E_{AS}$	36.2	mJ
Avalanche current		$I_{AR}$	3	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	2	mJ
Channel temperature		$T_{ch}$	150	$^\circ C$
Storage temperature range		$T_{stg}$	$-55\sim 150$	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	6.25	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	$^\circ C/W$

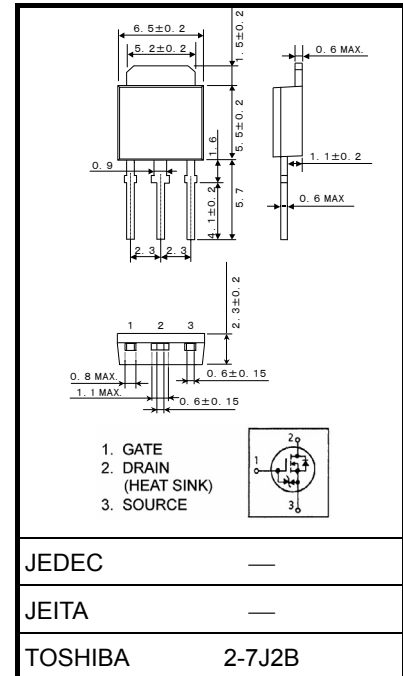
Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$ .

Note 2:  $V_{DD} = 50 V, T_{ch} = 25^\circ C, L = 6.7 mH, I_{AR} = 3 A, R_G = 25\Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.36 g (typ.)

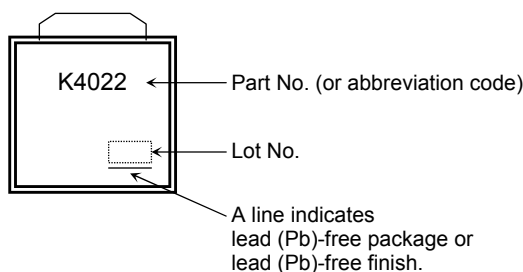
## Electrical Characteristics (Ta = 25°C)

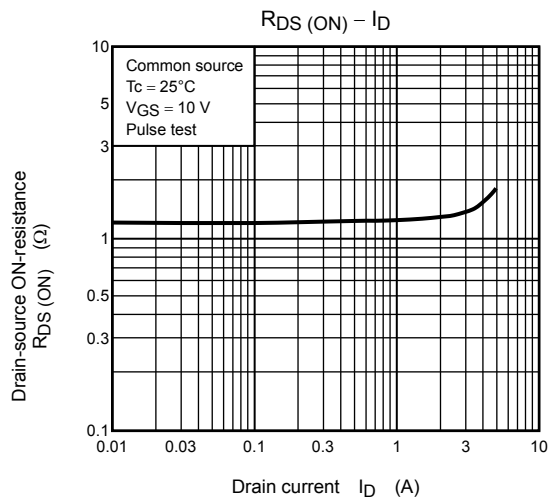
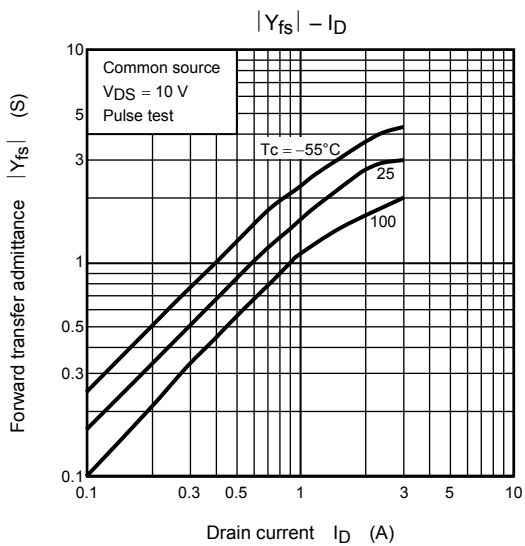
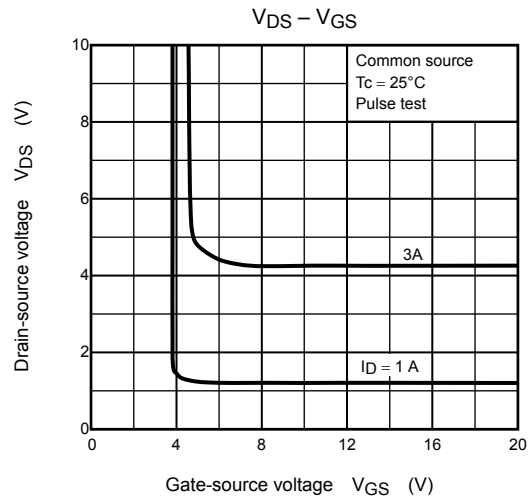
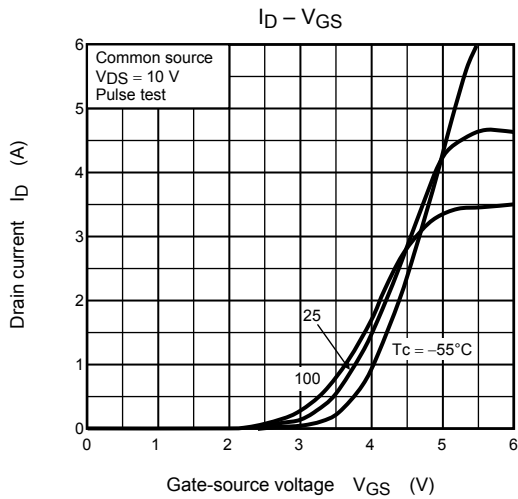
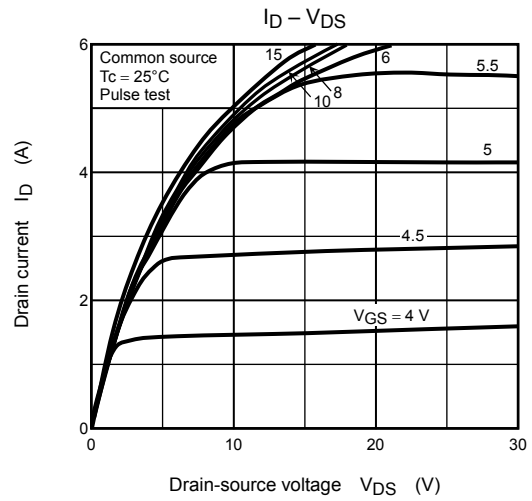
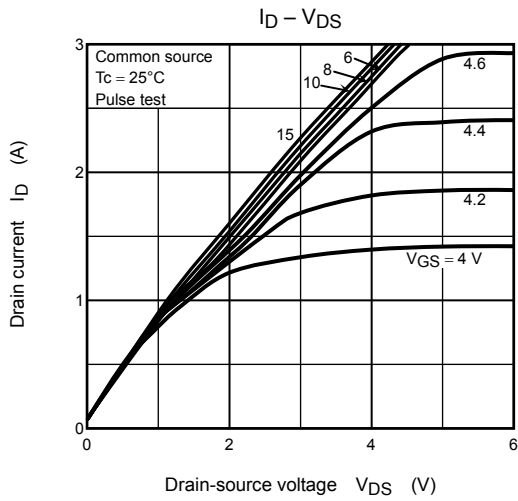
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cutoff current		$I_{DSS}$	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	250	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 1.5\text{ A}$	—	1.2	1.7	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 1.5\text{ A}$	0.5	2.2	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	267	—	pF
Reverse transfer capacitance		$C_{rss}$		—	32	—	
Output capacitance		$C_{oss}$		—	98	—	
Switching time	Rise time	$t_r$		—	5	—	ns
	Turn-on time	$t_{on}$		—	20	—	
	Fall time	$t_f$		—	5	—	
	Turn-off time	$t_{off}$		—	30	—	
Total gate charge		$Q_g$	$V_{DD} = 200\text{ V}, V_{GS} = 10\text{ V}, I_D = 3\text{ A}$	—	12	—	nC
Gate-source charge		$Q_{gs}$		—	6	—	
Gate-drain charge		$Q_{gd}$		—	6	—	

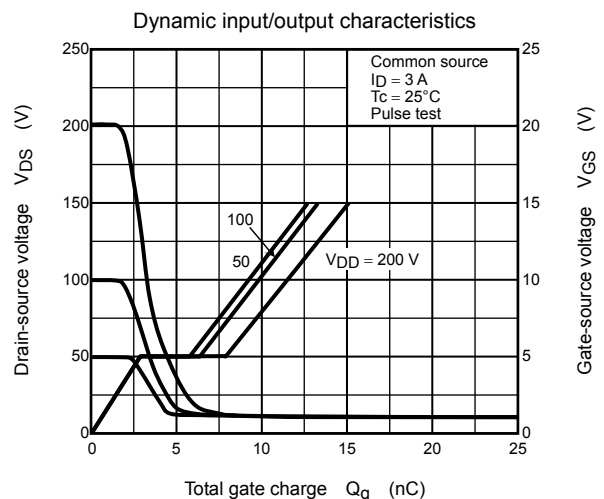
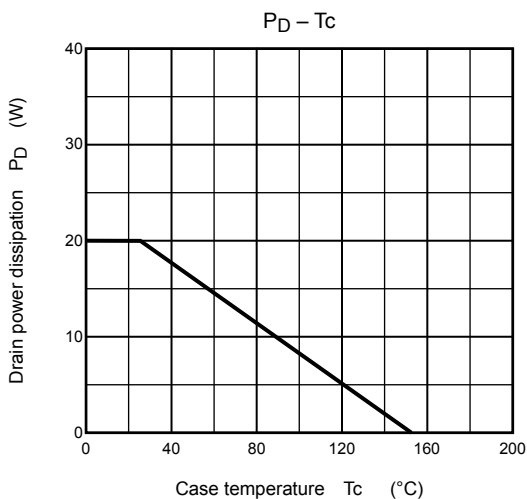
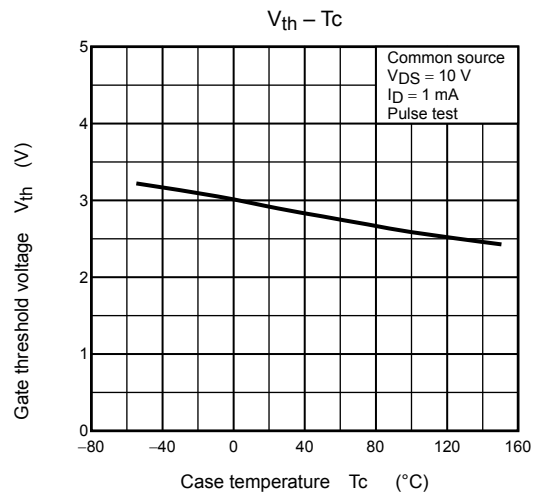
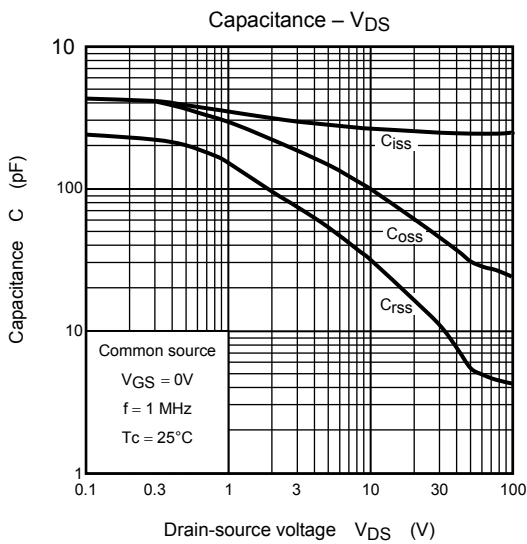
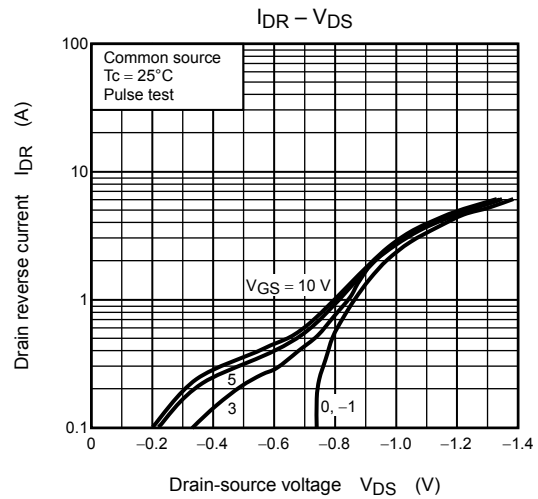
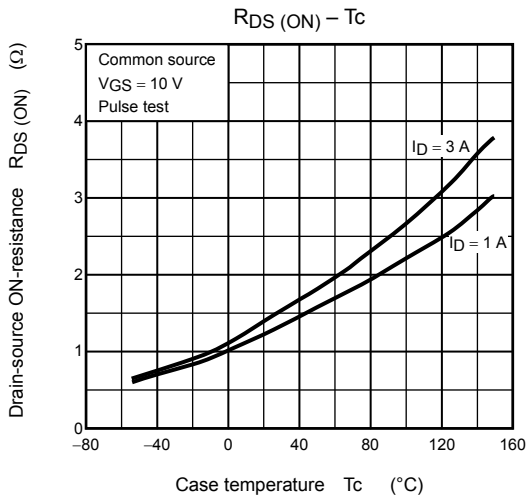
## Source-Drain Ratings and Characteristics (Ta = 25°C)

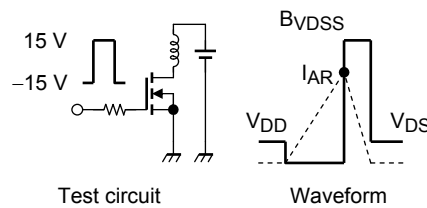
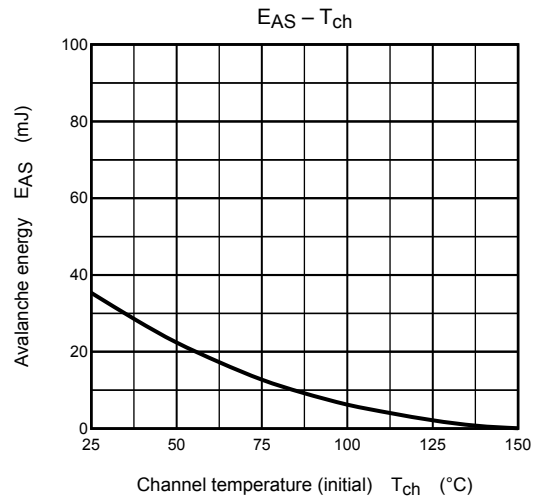
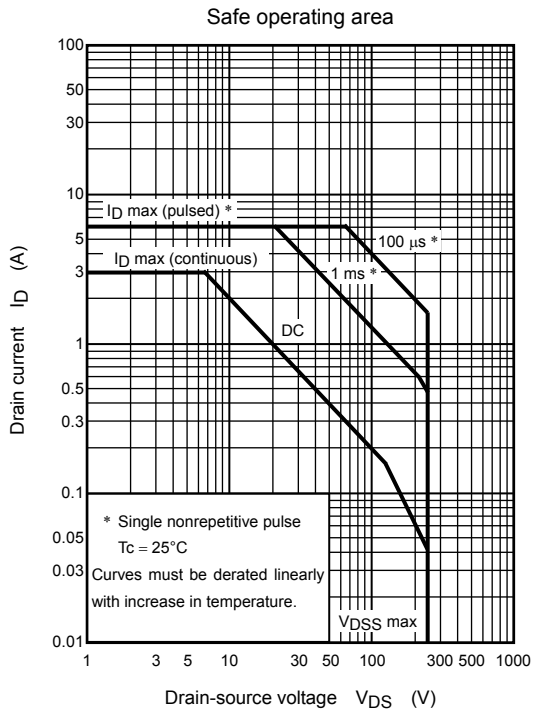
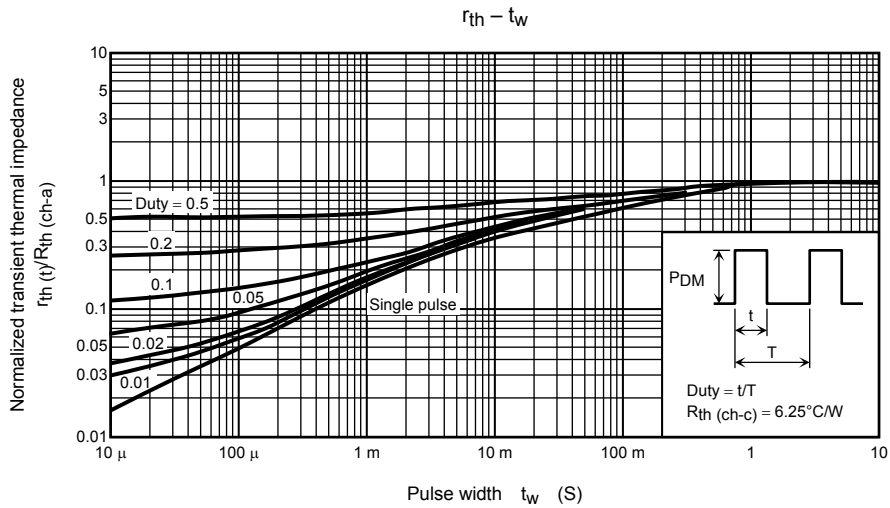
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	3	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	6	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 3\text{ A}, V_{GS} = 0\text{ V}$	—	—	-2.0	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 3\text{ A}, V_{GS} = 0\text{ V},$	—	125	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	470	—	nC

## Marking









$$R_G = 25 \Omega$$

$$V_{DD} = 50 V, L = 6.7 \text{ mH}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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